David Ferry

List of Publications by Year
in descending order

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264	6,805	71102	88630
papers	citations	41 h-index	70 g-index

274	274	274	3734
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Memristor Equations: Incomplete Physics and Undefined Passivity/Activity. , 2022, , 359-366.		0
2	A review of quantum transport in field-effect transistors. Semiconductor Science and Technology, 2022, 37, 043001.	2.0	11
3	Pathways to hot carrier solar cells. Journal of Photonics for Energy, 2022, 12, .	1.3	4
4	Wavepacket phase-space quantum Monte Carlo method. Journal of Computational Electronics, 2021, 20, 267-273.	2.5	7
5	High electric field transport in GaAs_{0.51}Sb_{0.49}. Semiconductor Science and Technology, 2021, 36, 045024.	2.0	3
6	Non-equilibrium longitudinal optical phonons and their lifetimes. Applied Physics Reviews, 2021, 8, .	11.3	9
7	Valley polarized conductance quantization in bilayer graphene narrow quantum point contact. Applied Physics Letters, 2021, 118, .	3.3	6
8	Why engineers are right to avoid the quantum reality offered by the orthodox theory? [point of view]. Proceedings of the IEEE, 2021, 109, 955-961.	21.3	8
9	The Role of Valley Degeneracy in Carrier Extraction in Valley Photovoltaic Solar Cells. , 2021, , .		0
10	Signature of Spin-Resolved Quantum Point Contact in p-Type Trilayer WSe₂ van der Waals Heterostructure. Nano Letters, 2021, 21, 7534-7541.	9.1	3
11	Special issue on Wigner functions in computational electronics and photonics. Journal of Computational Electronics, 2021, 20, 2019.	2.5	1
12	A Comprehensive Study of the Bridge Site and Substrate Relaxation Asymmetry for Methanethiol Adsorption on Au(111) at Low Coverage. ACS Omega, 2020, 5, 20874-20881.	3.5	2
13	Wigner functions in optoelectronics: Wave-packet phase-space Monte Carlo solver for waveguide-ring coupling. Journal of Applied Physics, 2020, 128, 153102.	2.5	1
14	Complex Systems in Phase Space. Entropy, 2020, 22, 1103.	2.2	4
15	Exploiting intervalley scattering to harness hot carriers in IIIâ€“V solar cells. Nature Energy, 2020, 5, 336-343.	39.5	45
16	Challenges, myths, and opportunities in hot carrier solar cells. Journal of Applied Physics, 2020, 128, .	2.5	21
17	Pulsed studies of intervalley transfer in Al0.35In0.65As : A paradigm for valley photovoltaics. Physical Review Materials, 2020, 4, .	2.4	3
18	The role of intervalley phonons in hot carrier transfer and extraction in type-II InAs/AlAsSb quantum-well solar cells. Semiconductor Science and Technology, 2019, 34, 094001.	2.0	14

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19	Investigating Quantum Coherence by Negative Excursions of the Wigner Quasi-Distribution. Applied Sciences (Switzerland), 2019, 9, 1344.	2.5	6
20	Electron transport in the solar-relevant InAlAs. Semiconductor Science and Technology, 2019, 34, 064003.	2.0	4
21	Wigner equation for general electromagnetic fields: The Weyl-Stratonovich transform. Physical Review B, 2019, 99, .	3.2	11
22	In search of a true hot carrier solar cell. Semiconductor Science and Technology, 2019, 34, 044001.	2.0	26
23	Hot Carrier Solar Cells based on Inter-Valley Phonon Scattering: A New Approach towards a Practical Solution. , 2019, , .		0
24	Relativistic Wigner functions in transition metal dichalcogenides. Journal of Computational Electronics, 2018, 17, 110-117.	2.5	10
25	Photosynthesis versus photovoltaics. Journal of Computational Electronics, 2018, 17, 313-318.	2.5	3
26	Information entropy and thermal entropy: apples and oranges. Journal of Computational Electronics, 2018, 17, 43-50.	2.5	12
27	Recent advances in Wigner function approaches. Applied Physics Reviews, 2018, 5, 041104.	11.3	159
28	Carrier statistics in graphene at high electric field. Semiconductor Science and Technology, 2017, 32, 025018.	2.0	4
29	Electron transport in some transition metal di-chalcogenides: MoS₂ and WS₂. Semiconductor Science and Technology, 2017, 32, 085003.	2.0	15
30	Memristor Equations: Incomplete Physics and Undefined Passivity/Activity. Fluctuation and Noise Letters, 2017, 16, 1771001.	1.5	15
31	Negative Differential Conductance & Hot-Carrier Avalanching in Monolayer WS2 FETs. Scientific Reports, 2017, 7, 11256.	3.3	18
32	Ferroelectric-Domain-Patterning-Controlled Schottky Junction State in Monolayer <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>MoS</mml:mi></mml:mrow><mml:mn>2</mml:mn></mml:msub></ Physical Review Letters, 2017, 118, 236801.	7.8	57
33	Dynamics of Current, Charge and Mass. Computational and Mathematical Biophysics, 2017, 5, 78-115.	1.1	11
34	Conductance fluctuations in high mobility monolayer graphene: Nonergodicity, lack of determinism and chaotic behavior. Scientific Reports, 2016, 6, 33118.	3.3	5
35	Conductance fluctuations in graphene in the presence of long-range disorder. Journal of Physics Condensed Matter, 2016, 28, 135302.	1.8	6
36	Electron velocity saturation and intervalley transfer in monolayer MoS2. Semiconductor Science and Technology, 2016, 31, 11LT01.	2.0	4

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37	Density dependence of the saturated velocity in graphene. Semiconductor Science and Technology, 2016, 31, 11LT02.	2.0	1
38	Energy relaxation of hot carriers in graphene via plasmon interactions. Journal of Computational Electronics, 2016, 15, 144-153.	2.5	0
39	Plasmon-mediated energy relaxation in graphene. Applied Physics Letters, 2015, 107, 262103.	3.3	3
40	Introduction to the special issue on Wigner functions. Journal of Computational Electronics, 2015, 14, 857-858.	2.5	1
41	Conductance fluctuations in graphene subjected to short-range disorder. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, 04E101.	1.2	3
42	Probing the quantumâ€“classical connection with open quantum dots. Physica Scripta, 2015, T165, 014010.	2.5	5
43	Phase-space functions: can they give a different view of quantum mechanics?. Journal of Computational Electronics, 2015, 14, 864-868.	2.5	10
44	Reversing hot-carrier energy-relaxation in graphene with a magnetic field. Applied Physics Letters, 2014, 104, 193115.	3.3	5
45	Scanning gate imaging of a disordered quantum point contact. Journal of Physics Condensed Matter, 2014, 26, 193202.	1.8	4
46	Conductance fluctuations in graphene nanoribbons. Journal of Computational Electronics, 2014, 13, 950-959.	2.5	6
47	Are there quantum jumps. International Journal of Modern Physics Conference Series, 2014, 33, 1460358.	0.7	0
48	Quantum transport beyond DC. Journal of Computational Electronics, 2013, 12, 317-330.	2.5	18
49	Use of the scattering matrix for device simulations. Journal of Computational Electronics, 2013, 12, 356-362.	2.5	5
50	Short-range potential scattering and its effect on graphene mobility. Journal of Computational Electronics, 2013, 12, 76-84.	2.5	21
51	Fast Energy Relaxation of Hot Carriers Near the Dirac Point of Graphene. Nano Letters, 2013, 13, 4305-4310.	9.1	29
52	Pseudopotential-based studies of electron transport in graphene and graphene nanoribbons. Journal of Physics Condensed Matter, 2013, 25, 473202.	1.8	58
53	Physical scales in the Wignerâ€“Boltzmann equation. Annals of Physics, 2013, 328, 220-237.	2.8	25
54	Nonergodicity and microscopic symmetry breaking of the conductance fluctuations in disordered mesoscopic graphene. Physical Review B, 2012, 86, .	3.2	27

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55	The role of substrate for transport in graphene. , 2012, , .		3
56	Simulating InP-based composite channel p-HEMTs with ultrashort gates for THz applications. , 2012, , .		1
57	Cellular Monte Carlo study lateral scaling impact of on the DC-RF performance of high-power GaN HEMTs. , 2012, , .		3
58	Transport in graphene on BN and SiC. , 2012, , .		6
59	Robust mesoscopic fluctuations in disordered graphene. Applied Physics Letters, 2012, 101, 093110.	3.3	18
60	Millimeter-wave power amplifier circuit-device simulations through coupled Harmonic Balance - Monte Carlo particle-based device simulator. , 2012, , .		3
61	Ohm's Law in a Quantum World. Science, 2012, 335, 45-46.	12.6	17
62	Terahertz-capability nanoscale InGaAs HEMT design guidelines by means of full-band Monte Carlo device simulations. , 2011, , .		0
63	Carrier Dynamics Investigation on Passivation Dielectric Constant and RF Performance of Millimeter-Wave Power GaN HEMTs. IEEE Transactions on Electron Devices, 2011, 58, 3876-3884.	3.0	11
64	Open quantum dotsâ€"probing the quantum to classical transition. Semiconductor Science and Technology, 2011, 26, 043001.	2.0	44
65	EXTRACTION OF GATE CAPACITANCE OF HIGH-FREQUENCY AND HIGH-POWER GaN HEMTs BY MEANS OF CELLULAR MONTE CARLO SIMULATIONS. International Journal of High Speed Electronics and Systems, 2011, 20, 423-430.	0.7	1
66	Scattering matrix approach to direct solution of the SchrÃ¶dinger equation. Journal of Computational Electronics, 2010, 9, 232-236.	2.5	0
67	Optimizing performance to achieve multiâ€terahertz operating frequencies in pseudomorphic HEMTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2502-2505.	0.8	0
68	RF and DC characterization of state-of-the-art GaN HEMT devices through cellular Monte Carlo simulations. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2445-2449.	0.8	0
69	NOISE AND BELL'S INEQUALITY. Fluctuation and Noise Letters, 2010, 09, 423-426.	1.5	1
70	The transport and quantum capacitance properties of epitaxial graphene. Applied Physics Letters, 2010, 96, 162101.	3.3	28
71	Aspect Ratio Impact on RF and DC Performance of State-of-the-Art Short-Channel GaN and InGaAs HEMTs. IEEE Electron Device Letters, 2010, , .	3.9	24
72	Generation of highly spin-polarized currents in cascaded InAs spin filters. Journal of Applied Physics, 2009, 105, .	2.5	9

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73	Quantum computing and probability. Journal of Physics Condensed Matter, 2009, 21, 474201.	1.8	4
74	Ballistic Transport in InP-Based HEMTs. IEEE Transactions on Electron Devices, 2009, 56, 2935-2944.	3.0	6
75	A method for performing fully quantum mechanical simulations ofÂgated silicon quantum wire structures. Journal of Computational Electronics, 2009, 8, 78-89.	2.5	1
76	Room temperature carrier transport in graphene. Journal of Computational Electronics, 2009, 8, 43-50.	2.5	52
77	Velocity saturation in intrinsic graphene. Journal of Physics Condensed Matter, 2009, 21, 344201.	1.8	109
78	Intrinsic mobility in graphene. Journal of Physics Condensed Matter, 2009, 21, 232204.	1.8	71
79	Physical Modeling of Microwave Transistors Using a Full-Band/Full-Wave Simulation Approach. , 2009, , .		3
80	Studies of electronâ€“phonon and phononâ€“phonon interactions in InN using ultrafast Raman spectroscopy. Journal of Physics Condensed Matter, 2009, 21, 174202.	1.8	12
81	Figures of merit in high-frequency and high-power GaN HEMTs. Journal of Physics: Conference Series, 2009, 193, 012040.	0.4	18
82	Transport in open quantum systems: comparing classical and quantum phase space dynamics. Journal of Computational Electronics, 2008, 7, 259-262.	2.5	3
83	Charge density variation with fin width in FinFETs: anÂapplication of supersymmetric quantum mechanics. Journal of Computational Electronics, 2008, 7, 14-19.	2.5	3
84	Towards the global modeling of InGaAs-based pseudomorphic HEMTs. Journal of Computational Electronics, 2008, 7, 187-191.	2.5	8
85	Calculation of Fin width for bulk inversion in Si FinFET byÂapplying supersymmetry. Journal of Computational Electronics, 2008, 7, 305-308.	2.5	2
86	Hot electron effects in ultra-short gate length InAs/InAlAs HEMTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 135-138.	0.8	1
87	Quo Vadis Nanoelectronics?. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 17-22.	0.8	7
88	Some Considerations on Nanowires in Nanoelectronics. IEEE Transactions on Electron Devices, 2008, 55, 2820-2826.	3.0	18
89	Nanowires in Nanoelectronics. Science, 2008, 319, 579-580.	12.6	110
90	The Upper Limit of the Cutoff Frequency in Ultrashort Gate-Length InGaAs/InAlAs HEMTs: A New Definition of Effective Gate Length. IEEE Electron Device Letters, 2008, 29, 306-308.	3.9	42

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91	Simulating Pseudomorphic HEMTs: Optimizing Performance to Achieve Multi-terahertz Operating Frequencies. , 2008, , .		0
92	DREAMS VERSUS REALITY: PLENARY DEBATE SESSION ON QUANTUM COMPUTING. Fluctuation and Noise Letters, 2008, 08, C27-C51.	1.5	0
93	Full-band cellular Monte Carlo simulations of terahertz high electron mobility transistors. Journal of Physics Condensed Matter, 2008, 20, 384201.	1.8	5
94	Nonlocal effects in semiconductor nanostructure transport. Journal of Physics Condensed Matter, 2008, 20, 454201.	1.8	3
95	Imaging classical and quantum structures in an open quantum dot using scanning gate microscopy. Journal of Vacuum Science & Technology B, 2008, 26, 1488.	1.3	3
96	Coupling-Induced Bipartite Pointer States in Arrays of Electron Billiards: Quantum Darwinism in Action?. Physical Review Letters, 2008, 101, 024102.	7.8	38
97	Linear and nonlinear conductance of ballistic quantum wires with hybrid confinement. Journal of Applied Physics, 2008, 103, 013701.	2.5	10
98	Cascade of Y-shaped spin filters in InGaAs/InAs/InGaAs quantum wells. Journal of Applied Physics, 2008, 104, 066106.	2.5	13
99	SEMICONDUCTOR DEVICE SCALING: PHYSICS, TRANSPORT, AND THE ROLE OF NANOWIRES. Selected Topics in Electornics and Systems, 2008, , 1-12.	0.2	0
100	MAGNETO-TRANSPORT IN OPEN QUANTUM DOT ARRAYS AT THE TRANSITION FROM LOW TO HIGH MAGNETIC FIELDS: REGULARITY AND CHAOS. International Journal of Modern Physics B, 2007, 21, 1288-1296.	2.0	4
101	Electron-density dependence of longitudinal-optical phonon lifetime in InN studied by subpicosecond time-resolved Raman spectroscopy. Journal of Physics Condensed Matter, 2007, 19, 236219.	1.8	6
102	Subpicosecond time-resolved Raman studies of electronâ€“longitudinal optical phonon interactions in InN. Applied Physics Letters, 2007, 90, 172108.	3.3	5
103	Draining of the Sea of Chaos: Role of Resonant Transmission and Reflection in an Array of Billiards. Physical Review Letters, 2007, 98, 204101.	7.8	38
104	Direct measurements of the lifetimes of longitudinal optical phonon modes and their dynamics in InN. Applied Physics Letters, 2007, 90, 152107.	3.3	17
105	Pulsed measurements of the nonlinear conductance of quantum point contacts. Applied Physics Letters, 2007, 90, 043103.	3.3	10
106	Simulation of Ultrasubmicrometer-Gate $hbox{In}_{0.52} hbox{Al}_{0.48}hbox{As/In}_{0.75}hbox{Ga}_{0.25}hbox{As/In}_{0.52}hbox{Al}_{0.48}hbox{As/InP}$ Pseudomorphic HEMTs Using a Full-Band Monte Carlo Simulator. IEEE Transactions on Electron Devices, 2007, 54, 2327-2338.	3.0	28
107	Kinetic Monte-Carlo simulations of germanium epitaxial growth on silicon. Journal of Computational Electronics, 2007, 5, 451-454.	2.5	1
108	The Rashba effect and non-Abelian phases in quantum wire devices. Journal of Computational Electronics, 2007, 6, 101-104.	2.5	5

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109	Classical and quantum mechanical transport simulations in open quantum dots. Journal of Computational Electronics, 2007, 6, 93-96.	2.5	7
110	Scanning Gate Imaging of Transport within an InGaAs QPC. AIP Conference Proceedings, 2007, , .	0.4	2
111	Spin Rotations and Non-Abelian Phases in Quantum Wire Networks. AIP Conference Proceedings, 2007, , .	0.4	1
112	Semiconductor Device Scaling: The Role of Ballistic Transport. Journal of Computational and Theoretical Nanoscience, 2007, 4, 1149-1152.	0.4	4
113	Subpicosecond time-resolved Raman studies of LO phonons in GaN: Dependence on photoexcited carrier density. Applied Physics Letters, 2006, 89, 112111.	3.3	100
114	Imaging of quantum interference patterns within a quantum point contact. Applied Physics Letters, 2006, 89, 242109.	3.3	23
115	Study of quantum point contact via low temperature scanning gate microscopy. Journal of Physics: Conference Series, 2006, 38, 79-82.	0.4	13
116	Fully Quantum Mechanical Simulations of Gated Silicon Quantum Wire Structures: Investigating the Effects of Changing Wire Cross-Section on Transport. Journal of Physics: Conference Series, 2006, 38, 87-90.	0.4	11
117	Imaging of quantum interference patterns within a quantum point contact. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 682-685.	2.7	1
118	Subpicosecond Raman studies of electric-field-induced optical phonon instability in an In0.53Ga0.47As-based semiconductor nanostructure. Journal of Physics Condensed Matter, 2006, 18, 7961-7974.	1.8	6
119	Complexities in modeling the metal to molecule interface. Journal of Vacuum Science & Technology B, 2006, 24, 1987.	1.3	2
120	Indium arsenide quantum wire trigate metal oxide semiconductor field effect transistor. Journal of Applied Physics, 2006, 99, 054503.	2.5	14
121	Wigner transport models of the electron-phonon kinetics in quantum wires. Physical Review B, 2006, 74, .	3.2	28
122	Large capacitance in the nanosecond-scale transient response of quantum point contacts. Applied Physics Letters, 2006, 89, 083103.	3.3	26
123	Electron spin filter based on Rashba spin-orbit coupling. Applied Physics Letters, 2006, 89, 172115.	3.3	33
124	Subpicosecond transient Raman scattering studies of field-induced electron transport in an In0.53Ga0.47As based pâ€“iâ€“n nanostructure: direct observation of the effects of electron momentum randomization. Journal of Physics Condensed Matter, 2006, 18, L585-L592.	1.8	1
125	Dephasing due to coupling to the external environment in open quantum-dot arrays. Journal of Physics Condensed Matter, 2005, 17, L351-L357.	1.8	12
126	Theoretical Evidence of Spontaneous Spin Polarization in GaAs/AlGaAs Split-Gate Heterostructures. Journal of Computational Electronics, 2005, 4, 125-128.	2.5	0

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127	Detection of non-equilibrium longitudinal optical phonons in InN and its consequences. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2324-2327.	0.8	0
128	High-field electron transport in AlGaN/GaN heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2564-2568.	0.8	6
129	50-Î©-matched system for low-temperature measurements of the time-resolved conductance of low-dimensional semiconductors. Review of Scientific Instruments, 2005, 76, 113905.	1.3	8
130	Magnetoresistance experiments and quasi-classical calculations regarding backscattering in open quantum dots. AIP Conference Proceedings, 2005, , .	0.4	0
131	Einselection and the quantum to classical transition in quantum dots. Journal of Physics Condensed Matter, 2005, 17, S1017-S1036.	1.8	21
132	Electron-Phonon Interaction of Wurtzite GaN and Its Effect on High Field Transport. AIP Conference Proceedings, 2005, , .	0.4	0
133	Picosecond Raman Studies of Electron and Hole Velocity Overshoots In a GaAs-based p-i-n Semiconductor Nanostructure. AIP Conference Proceedings, 2005, , .	0.4	0
134	Kinetic lattice Monte Carlo simulations of germanium epitaxial growth on the silicon (100) surface incorporating Siâ€“Ge exchange. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1821.	1.6	4
135	Observation of large electron drift velocities in InN by ultrafast Raman spectroscopy. Applied Physics Letters, 2005, 86, 222103.	3.3	70
136	Imaging of integer quantum Hall edge state in a quantum point contact via scanning gate microscopy. Physical Review B, 2005, 72, .	3.2	65
137	Scanning gate microscopy investigations on an InGaAs quantum point contact. Applied Physics Letters, 2005, 87, 223501.	3.3	39
138	Spin polarization in GaAs/Al0.24Ga0.76As heterostructures. Molecular Simulation, 2005, 31, 797-800.	2.0	5
139	Phonon-assisted ballistic to diffusive crossover in silicon nanowire transistors. Journal of Applied Physics, 2005, 98, 094303.	2.5	59
140	Quantum modelling of particleâ€“particle interactions in SOI MOSFETs. Semiconductor Science and Technology, 2004, 19, S238-S240.	2.0	3
141	Open-system nonequilibrium Green's functions and quantum transport in the transient regime. Semiconductor Science and Technology, 2004, 19, S220-S222.	2.0	7
142	Resonant tunneling behavior and discrete dopant effects in narrow ultrashort ballistic silicon-on-insulator metal-oxide-semiconductor field-effect transistors. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2039.	1.6	2
143	Unified particle approach to Wigner-Boltzmann transport in small semiconductor devices. Physical Review B, 2004, 70, .	3.2	146
144	Efficient quantum three-dimensional modeling of fully depleted ballistic silicon-on-insulator metal-oxide-semiconductor field-effect-transistors. Journal of Applied Physics, 2004, 95, 7954-7960.	2.5	53

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145	Einselection in Action: Decoherence and Pointer States in Open Quantum Dots. Physical Review Letters, 2004, 93, 026803.	7.8	74
146	Open system evolution and â€œmemory dressingâ€• Physical Review A, 2004, 69, .	2.5	19
147	Magnetically induced Bragg scattering of electrons in quantum-dot crystals. Physical Review B, 2004, 70, .	3.2	19
148	Field-induced nonequilibrium electron distribution and electron transport in a high-quality InN thin film grown on GaN. Applied Physics Letters, 2004, 84, 3681-3683.	3.3	27
149	Observation of nonequilibrium longitudinal optical phonons in InN and its implications. Applied Physics Letters, 2004, 84, 3849-3851.	3.3	9
150	High field transport in GaN/AlGaN heterostructures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2045.	1.6	44
151	Full Quantum Mechanical Simulation of Ultra-Small Silicon Devices in Three-Dimensions: Physics and Issues. Journal of Computational Electronics, 2004, 3, 355-358.	2.5	2
152	A Quantum Many-Body Density Matrix Model for Sub-Femtosecond Transport in Mesoscopic Structures. Journal of Computational Electronics, 2004, 3, 359-362.	2.5	1
153	Dreams Versus Reality: Plenary Debate Session on Quantum Computing. Quantum Information Processing, 2003, 2, 449-472.	2.2	4
154	What mesoscopic structures really â€œrememberâ€• insufficiency of the open boundary approximation. Superlattices and Microstructures, 2003, 34, 367-370.	3.1	3
155	Quantum transport and memory effects in mesoscopic structures. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 19, 71-76.	2.7	7
156	Transport in quantum dots. Materials Today, 2003, 6, 32-37.	14.2	4
157	Green's function approach for transport calculation in a In0.53Ga0.47As/In0.52Al0.48As modulation-doped heterostructure. Physica Status Solidi (B): Basic Research, 2003, 239, 103-109.	1.5	3
158	Microwave investigations of backscattering in open quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1321-1324.	0.8	2
159	Interference and interactions in open quantum dots. Reports on Progress in Physics, 2003, 66, 583-632.	20.1	58
160	Greenâ€™s function approach for transport calculation in a In0.53Ga0.47As/In0.52Al0.48As modulation-doped heterostructure. Journal of Applied Physics, 2003, 93, 3359-3363.	2.5	5
161	Dual computational basis qubit in semiconductor heterostructures. Applied Physics Letters, 2003, 83, 1453-1455.	3.3	4
162	Demonstration of a reflective coupling diode in a coupled waveguide structure. Journal of Applied Physics, 2003, 93, 6402-6404.	2.5	1

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163	Large electric-field induced electron drift velocity observed in an InxGa1â^'xAs-based pâ€“iâ€“n semiconductor nanostructure at T=300 K. Applied Physics Letters, 2003, 83, 1438-1440.	3.3	6
164	Memory effects and nonequilibrium transport in open many-particle quantum systems. Physical Review E, 2003, 67, 066122.	2.1	21
165	Greenâ€™s function approach for transport calculation in a In[sub 0.53]Ga[sub 0.47]As/In[sub 0.52]Al[sub 0.48]As modulation-doped heterostructure. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1903.	1.6	2
166	Generalized interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1891.	1.6	4
167	Semiconductor waveguide inversion in disordered narrow band-gap materials. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1924.	1.6	0
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169	NONEQUILIBRIUM TRANSPORT IN NANOSCALE SEMICONDUCTOR DEVICES. , 2003, , .		1
170	Partial-trace-free time-convolutionless equation of motion for the reduced density matrix. Physical Review E, 2002, 66, 016131.	2.1	23
171	Three-dimensional simulations of ultrasmall metalâ€“oxideâ€“semiconductor field-effect transistors: The role of the discrete impurities on the device terminal characteristics. Journal of Applied Physics, 2002, 91, 3737-3740.	2.5	27
172	Adiabatic switching in coupled quantum dot systems facilitated by the coexistence of â€œmolecularâ€•and â€œatomicâ€•states. Applied Physics Letters, 2002, 80, 4440-4442.	3.3	1
173	Interaction corrections to transport due to quasibound states in open quantum dots. Applied Physics Letters, 2002, 81, 3861-3863.	3.3	6
174	Response to â€œComment on â€˜Quantum waveguide array generator for performing Fourier transforms: Alternate route to quantum computingâ€™â€Šâ€•[Appl. Phys. Lett. 80, 2419 (2002)]. Applied Physics Letters, 2002, 80, 2420-2420.	3.3	0
175	Magnetically and electrically tunable semiconductor quantum waveguide inverter. Applied Physics Letters, 2002, 81, 4284-4286.	3.3	27
176	Tunneling and Nonhyperbolicity in Quantum Dots. Physical Review Letters, 2002, 88, 236804.	7.8	72
177	Simultaneous observation of electron and hole velocity overshoots in an Al0.3Ga0.7As-based pâ€“iâ€“n semiconductor nanostructure. Applied Physics Letters, 2002, 81, 3999-4001.	3.3	4
178	The persistence of eigenstates in open quantum dots. Applied Physics Letters, 2002, 81, 129-131.	3.3	53
179	Title is missing!. Journal of Computational Electronics, 2002, 1, 251-255.	2.5	0
180	QUANTUM TRANSPORT IN SEMICONDUCTOR DEVICES. International Journal of High Speed Electronics and Systems, 2001, 11, 363-385.	0.7	7

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181	Coupling-driven transition from multiple to single-dot interference in open quantum-dot arrays. Physical Review B, 2001, 64, .	3.2	25
182	Quantum waveguide array generator for performing Fourier transforms: Alternate route to quantum computing. Applied Physics Letters, 2001, 79, 2823-2825.	3.3	12
183	Quasi-one-dimensional transport characteristics of ridge-type InGaAs quantum-wire field-effect transistors. Applied Physics Letters, 2001, 79, 371-373.	3.3	11
184	Confinement-induced enhancement of electron-electron interactions in open quantum-dot arrays. Physical Review B, 2001, 63, .	3.2	15
185	Magnetically switched quantum waveguide qubit. Applied Physics Letters, 2001, 79, 2214-2215.	3.3	34
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